Am27X512

Advanced Micro Devices

512 Kilobit (65,536 x 8-Bit) CMOS ExpressROM Device

DISTINCTIVE CHARACTERISTICS

- As an OTP EPROM alternative:
 - Factory optimized programming
 - Fully tested and guaranteed
- As a Mask ROM alternative:
 - Shorter leadtime
 - Lower volume per code
- Fast access time
 - 70 ns
- Single +5 V power supply
- Compatible with JEDEC-approved EPROM pinout
- **■** ±10% power supply tolerance

- High noise immunity
- Low power dissipation
 - 100 μA maximum CMOS standby current
- Available in Plastic Dual In-Line Package (PDIP), Plastic Leaded Chip Carrier (PLCC), and Thin Small Outline Package (TSOP)
- Latch-up protected to 100 mA from −1 V to Vcc +1 V
- Versatile features for simple interfacing
 - Both CMOS and TTL input/output compatibility
 - Two line control functions

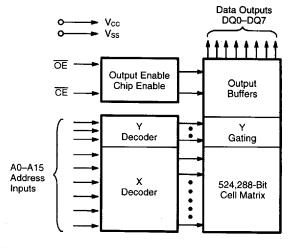
GENERAL DESCRIPTION

The Am27X512 is a factory programmed and tested OTP EPROM. It is programmed after packaging prior to final test. Every device is rigorously tested under AC and DC operating conditions to your stable code. It is organized as 65,536 by 8 bits and is available in plastic dual in-line (PDIP), plastic leaded chip carrier (PLCC), and thin small outline (TSOP) packages. ExpressROM devices provide a board-ready memory solution for medium to high volume codes with short leadtimes. This offers m⊱nufacturers a cost-effective and flexible alternative to ⊙TP EPROMs and mask programmed ROMs.

Access times as fast as 70 ns allow operation with highperformance microprocessors with reduced WAIT states. The Am27X512 offers separate Output Enable (OE) and Chip Enable (OE) controls, thus eliminating bus contention in a multiple bus microprocessor system.

AMD's CMOS process technology provides high speed, low power, and high noise immunity. Typical power consumption is only 80 mW in active mode, and 100 μW in standby mode.

BLOCK DIAGRAM



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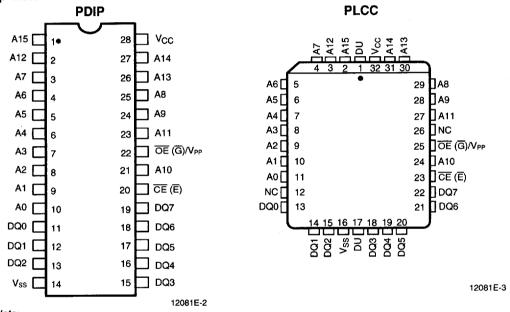
Publication# 12081 Rev. E Amendment/0 Issue Date: May 1995

PRODUCT SELECTOR GUIDE

Family Part No.				Am27X512	2	
Ordering Part No: Vcc±5%					:	-255
V _{CC} ± 10%	-70	-90	-120	-150	-200	
Max Access Time (ns)	70	90	120	150	200	250
CE (E) Access (ns)	70	90	120	150	200	250
OE (G) Access (ns)	70	40	50	65	75	100

CONNECTION DIAGRAMS

Top View



Note:

TSOP* 32 31 30 NC OE/V_{PP} □ 0 2 A10 A11 CE/PGM Α9 4 5 A8 □ 07 29 28 27 26 25 24 23 22 21 20 06 A13 6 7 **O**5 NC 04 A14 8 О3 Vcc 9 v_{ss} A15 10 02 NC 01 A12 11 00 12 **A7** NC 13 Α6 Α5 14 19 A0 15 A1 18 A4 АЗ 16 A2

*Contact local AMD sales office for package availability

Standard Pinout

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^{1.} JEDEC nomenclature is in parentheses.

PIN DESIGNATIONS

A0-A15

= Address Inputs

CE (E)

= Chip Enable Input

DQ0-DQ7 DU

= Data Inputs/Outputs

NC

= No External Connection (Do Not Use)

OE (G)

= No Internal Connection

OE (G)

= Output Enable Input

Vcc

= Vcc Supply Voltage

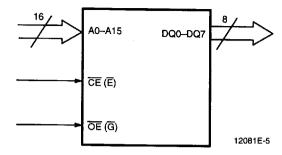
 V_{PP}

= Program Voltage Input

 V_{SS}

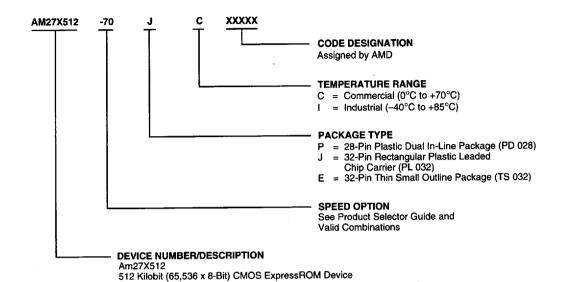
= Ground

LOGIC SYMBOL



ORDERING INFORMATION Standard Products

AMD standard products are available in several packages and operating ranges. The ordering number (Valid Combination) is formed by a combination of:



Valid Combinations					
AM27X512-70					
AM27X512-90]				
AM27X512-120	PC, JC, PI, JI, EC. EI				
AM27X512-150	7 20, 21				
AM27X512-200					
AM27X512-255	7				

Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations and to check on newly released combinations.

FUNCTIONAL DESCRIPTION Read Mode

The Am27X512 has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip Enable (\overline{CE}) is the power control and should be used for device selection. Output Enable \overline{OE} is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that addresses are stable, address access time (t_{ACC}) is equal to the delay from \overline{CE} to output (t_{CE}). Data is available at the outputs toe after the falling edge of \overline{OE} , assuming that \overline{CE} has been LOW and addresses have been stable for at least t_{ACC}—toe.

Standby Mode

The Am27X512 has a CMOS standby mode which reduces the maximum V_{CC} current to 100 μ A. It is placed in CMOS-standby when \overline{CE} is at $V_{CC} \pm 0.3$ V. The Am27X512 also has a TTL-standby mode which reduces the maximum V_{CC} current to 1.0 mA. It is placed in TTL-standby when \overline{CE} is at V_{IH} . When in standby mode, the outputs are in a high-impedance state, independent of the \overline{OE} input.

Output OR-Tieing

To accommodate multiple memory connections, a twoline control function is provided to allow for:

- Low memory power dissipation
- Assurance that output bus contention will not occur

It is recommended that $\overline{\text{CE}}$ be decoded and used as the primary device-selecting function, while $\overline{\text{OE/V}_{PP}}$ be made a common connection to all devices in the array and connected to the READ line from the system control bus. This assures that all deselected memory devices are in low-power standby mode and that the output pins are only active when data is desired from a particular memory device.

System Applications

During the switch between active and standby conditions, transient current peaks are produced on the rising and falling edges of Chip Enable. The magnitude of these transient current peaks is dependent on the output capacitance loading of the device. At a minimum, a 0.1 µF ceramic capacitor (high frequency, low inherent inductance) should be used on each device between Vcc and Vss to minimize transient effects. In addition, to overcome the voltage drop caused by the inductive effects of the printed circuit board traces on ExpressROM device arrays, a 4.7-µF bulk electrolytic capacitor should be used between Vcc and Vss for each eight devices. The location of the capacitor should be close to where the power supply is connected to the array.

MODE SELECT TABLE

Mode	Pins CE	ŌĒ/Vpp	Outputs
Read	VIL	VIL	DOUT
Output Disable	X	ViH	Hi-Z
Standby (TTL)	Viн	x	Hi-Z
Standby (CMOS)	Vcc ± 0.3 V	Х	Hi-Z

Note:

1. X = Either VIH or VIL



ABSOLUTE MAXIMUM RATINGS

7.20020.2 ····
Storage Temperature OTP Products65°C to +125°C
Ambient Temperature with Power Applied55°C to +125°C
Voltage with Respect to V_{SS} All pins except V_{CC} -0.6 V to V_{CC} + 0.6 V
Vcc0.6 V to +7.0 V

Note:

 Minimum DC voltage on input or I/O pins is -0.5 V. During transitions, the inputs may overshoot V_{SS} to -2.0 V for periods of up to 20 ns. Maximum DC voltage on input and I/O pins is V_{CC} + 0.5 V which may overshoot to V_{CC} + 2.0 V for periods up to 20 ns.

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure of the device to absolute maximum rating conditions for extended periods may affect device reliability.

OPERATING RANGES

•. •	
Commercial (C) Devices Ambient Temperature (T _A)	0°C to +70°C
Industrial (I) Devices Ambient Temperature (T _A)	40°C to +85°C
Supply Read Voltages Vcc for Am27X512-255	+4.75 V to +5.25 V
Vcc for all other valid combinations	+4.50 V to +5.50 V
O	i-is basinaa which the

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC CHARACTERISTICS over operating range unless otherwise specified (Notes 1, 2 and 4)

Parameter Symbol	Parameter Description	Test Conditions	Min	Max	Unit
VoH	Output HIGH Voltage	Іон = – 400 μΑ	2.4	 	V
Vol	Output LOW Voltage	lo _L = 2.1 mA	_	0.45	v
ViH	Input HIGH Voltage		2.0	Vcc+ 0.5	v
VIL	Input LOW Voltage		-0.5	+0.8	V
lu	Input Load Current	Vin = 0 V to +Vcc		1.0	μА
lto	Output Leakage Current	Vout = 0 V to +Vcc		1.0	μА
lcc ₁	Vcc Active Current (Note 3)	CE = V _{IL} f = 10 MHz, lout = 0 mA		30	mA
lcc2	Vcc TTL Standby Current	CE = V _{IH}		1.0	mA
Іссз	Vcc CMOS Standby Current	CE = V _{CC} ± 0.3 V	- 	100	μА

Notes:

- 1. VCC must be applied simultaneously or before VPP, and removed simultaneously or after VPP.
- 2. Caution: the Am27X512 must not be removed from (or inserted into) a socket when VCC or VPP is applied.
- 3. ICC1 is tested with $\overline{OE}/V_{PP} = V_{IH}$ to simulate open outputs.
- Minimum DC Input Voltage is -0.5 V. During transitions, the inputs may overshoot to -2.0 V for periods less than 20 ns.
 Maximum DC Voltage on output pins is V_{CC} + 0.5 V, which may overshoot to V_{CC} + 2.0 V for periods less than 20 ns.

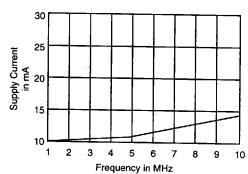


Figure 1. Typical Supply Current vs. Frequency Vcc = 5.5 V, T = 25°C

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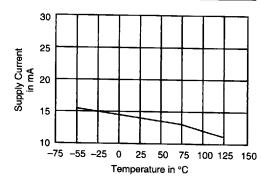


Figure 2. Typical Supply Current vs. Temperature Vcc = 5.5 V, f = 10 MHz

12081E-7



CAPACITANCE

			PD	028	PL	032	TS	032	
Parameter Symbol	Parameter Description	Test Conditions	Тур	Max	Тур	Max	Тур	Max	Unit
Cin	Input Capacitance	V _{IN} = 0 V	6	10	9	12	10	12	рF
Соит	Output Capacitance	V _{OUT} = 0 V	8	10	9	12	12	14	pF

Notes:

- 1. This parameter is only sampled and not 100% tested.
- 2. $T_A = +25^{\circ}C$, f = 1 MHz.

SWITCHING CHARACTERISTICS over operating range unless otherwise specified (Notes 1, 3, and 4)

Parameter							Am27	X512			
Sym JEDEC	bols Standard	Parameter Description	Test Conditions		-70	-90	-120	-150	-200	-255	Unit
tavov	trcc	Address to	CE = OE =VIL	Min				·			
		Output Delay		Max	70	90	120	150	200	250	ns
tELOV	tce	Chip Enable to	OE = VIL	Min							
12241		Output Delay		Max	70	90	120	150	200	250	ns
tgLQV	toe	Output Enable to	CE = VIL	Min	1				<u></u> _		l .
		Output Delay		Max	40	40	50	50	50	50	ns
tenoz	tor	Chip Enable HIGH or		Min	0	0	0	0	0	0	i
tgнаz	(Note 2)	Output Enable HIGH, whichever comes first, to Output Float		Max	25	30	30	30	30	30	ns
taxox	tон	Output Hold from		Min	0	0	0	0	0	0	1
		Addresses, CE, or OE, whichever occurred first		Max	-	_		_		_	ns

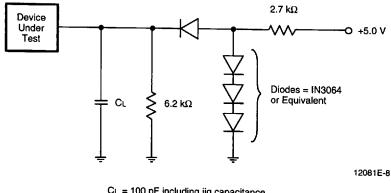
Notes:

- 1. VCC must be applied simultaneously or before VPP, and removed simultaneously or after VPP.
- 2. This parameter is only sampled and not 100% tested.
- 3. Caution: The Am27X512 must not be removed from (or inserted into) a socket or board when Vpp or Vcc is applied.
- 4. Output Load: 1 TTL gate and CL = 100 pF

Input Rise and Fall Times: 20 ns Input Pulse Levels: 0.45 V to 2.4 V

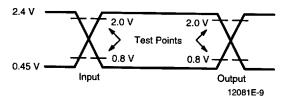
Timing Measurement Reference Level: 0.8 V and 2 V for inputs and outputs

SWITCHING TEST CIRCUIT



C_L = 100 pF including jig capacitance

SWITCHING TEST WAVEFORM



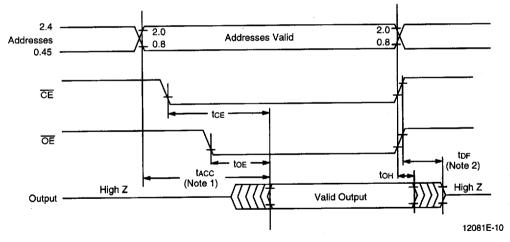
AC Testing: Inputs are driven at 2.4 V for a logic "1" and 0.45 V for a logic "0". Input pulse rise and fall times are < 20 ns.

KEY TO SWITCHING WAVEFORMS

WAVEFORM	INPUTS	OUTPUTS
	Must be Steady	Will be Steady
	May Change from H to L	Will be Changing from H to L
	May Change from L to H	Will be Changing from L to H
	Don't Care, Any Change Permitted	Changing, State Unknown
>>	Does Not Apply	Center Line is High- Impedance "Off" State

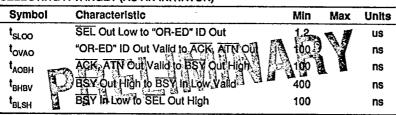
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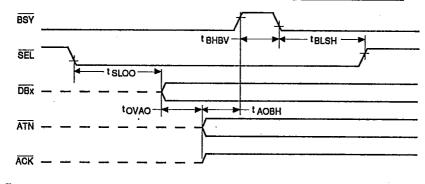
SWITCHING WAVEFORMS



Notes:

- 1. \overline{OE} may be delayed up to tACC-tOE after the falling edge of the addresses without impact on tACC.
- 2. tpF is specified from \overline{OE} or \overline{CE} , whichever occurs first.

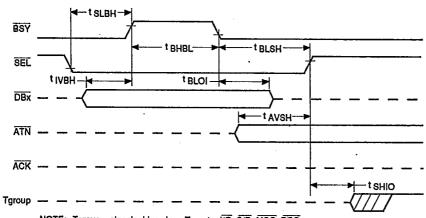




NOTE: Tgroup = signals driven by a Target = I/O, C/D, MSG, REQ

RESPONSE TO SELECTION (AS A TARGET)

Symbol	Characteristic	Min	Max	Units
t _{SLBH}	SEL In Low to BSY In High	A 1		ns
t _{iVBH}	"OR-ED" ID Valid In to BSY In High	A Fig.	A	ns
t _{BHBL}		oly 19.41	200	us
t _{BLOI}	BSY Out Low to "OR-ED" D Invalid in	0		ns
t _{BLSH}	BSY Out Low to SEL In High	0		ns
tavsh T	ATN Valid In to SEL In High	0		ns
t _{SHIO}	SEL in High to Tgroup Out	100		ns



NOTE: Tgroup = signals driven by a Target = I/O, C/D, MSG, REQ

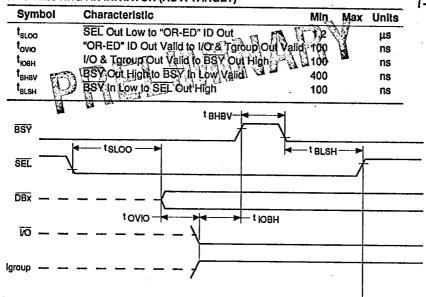
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RESELECTING AN INITIATOR (AS A TARGET)

T-52-33-27



NOTE: Tgroup = signals driven by a Target = $\overline{C/D}$, \overline{MSG} , \overline{REQ} Igroup = signals driven by an Initiator = ATN, ACK

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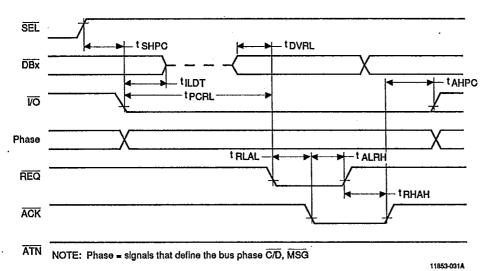
			<u> </u>	TION (AS AN INITIATOR)		
Units	Max	Min		stic	ol Character	Symbol
ns		_ Q_ (*)		to BSY In High		t _{SLBH}
ns	3	(0)	. 64	Valid In to BSY In High		t _{IVBH}
ns		01	MB B	to BSY In High 💢 🐧 🧌	1/O In Low	t _{ILBH}
ns		100°	oup Out	ID Valld , BSY High to Igrou	SEL Low,	t _{BHAO}
ns		100	<i>ऀ</i> ∄ 19 .	Qut to BSY Out Low	Igroup Vali	t _{AVBL}
μs	200	0.4		h to BSY Out Low 1 12	BSY In Hig	t _{BHBL}
ns		0	in	w to "OR-ED" ID Invalid In		t _{BLOI} ,
ns		0		ywtò SEL In High		t _{BLSH}
nş		0		n to BSY Out High	SEA In Hig	t _{shbh}
1 SHBI		SH P	t BLS	1BHBL	1 SLBH	BSY
	- .	<u>*</u> 		1 BLO1	tiven	DBx —
			AVBL	X \		Igroup —
				■ BHAO, I	100	1/0
			- tAVBL		t _{ILBH}	_

Tgroup = signals driven by a Target = C/D, MSG, REQ Igroup = signals driven by an Initiator = ATN, ACK *** BSY will still be driven by the reselecting target.

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RECEIVE ASYNCHRONOUS INFORMATION TRANSFER IN (ACTING AS AN INITIATOR)

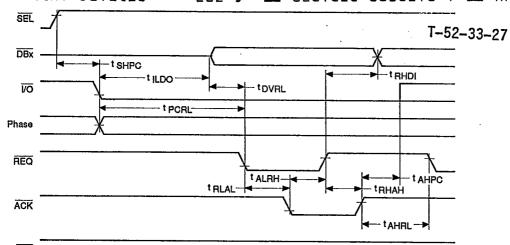
Symbol	Characteristic	Min	Max	Units	T-52-33-27
t _{SHPC}	SEL In High to Phase Change In	0		ns	1-32-33-27
t _{ILDT}	I/O in Low to Data Bus TRISTATE	0	125	ns	
tpcsl	Phase Change In to REQ In Low	1400		ns	
t _{DVRL}	Data Valid In to REQ In Low	0 1		ns	
t _{RLAL}	REO In Low to ACK Out Low	0	175	ns	
t _{ALDI}	ACK Out Low to Data Invalid in	0		ns	
t _{ALRH}	ACK Out Low to REQ In High	0		ns	
t _{RHAH}	REQ In High to ACK Out High	0	175	ns	
tAHPC	ACK Out High to Phase Change In	0		ns	





SEND ASYNCHRONOUS INFORMATION TRANSFER IN (ACTING AS A TARGET)

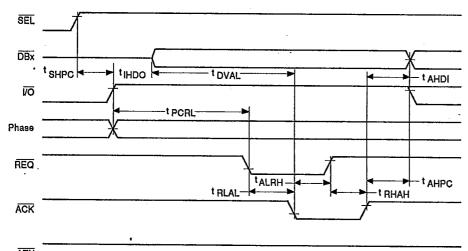
Symbol	Characteristic	Min	Max	Units
t _{SHPC}	SEL In High to Phase Change Out	100	. #	ns
t _{ILDO}	1/O Out Low to Data Out	800		ns
t _{DVRL}	Data Out Valid to REQ Out Low	∏55 🔭		ns
t _{PCRL}	Phase Change Out to REQ Our Low	500	4	ns
t _{RLAL}	REQ Out Low to ACR in Low	0		ns
t _{ALRH}	ACK in Low to REO Out High	0	175	ns
tALDI	ACK in Low to Data Out Invalid	0		ns
t _{RHAH}	REC Out High to ACK In High	0		ns
t _{AHPC}	ACK In High to Phase Change Out	100		ns
t _{AHRL}	ACK In High to REQ Out Low	0	175	ns



ATN NOTE: Phase = signals that define the bus phase C/D, MSG

SEND ASYNCHRONOUS INFORMATION TRANSFER OUT (ACTING AS AN INITIATOR)

Symbo	I Characteristic	Min	Max	Units
t _{SHPC}	SEL In High to Phase Change In	0	~0	ns
t _{IHDO}	I/O In High to Data Out	A ST		ns
t _{PCRL}	Phase Change In to REQ In Low	400	LI D	ns
t _{rlal}	REQ In Low to ACK Out Low	1 0 1	175	ns
t _{DVAL}	Data Out Valid to ACK Out Low	55	•	ns
t _{ALRH}	ACK Out Low to REO In High	0		ns
t _{rhah}	REO In High to ACK Out High	0:	175	ns
t _{RHDI}	REQ In High to Data Out Invalid	0		ns
t _{AHPC}	ACK Out High to Phase Change In	0		ns



NOTE: Phase = signals that define the bus phase C/D, MSG

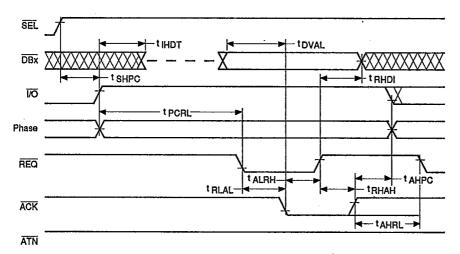
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RECEIVE ASYNCHRONOUS INFORMATION TRANSFER OUT (ACTING AS A TARGET)

Symbo	ol	Characteristic	Min	Max	Units	T 50 00
t _{SHPC}		SEL In High to Phase Change Out	100		ns	T-52-33-27
t _{IHDT}		I/O Out High to Data Bus TRISTATE	0-	4	ns	
t _{PCRL}		Phase Change to REQ Out Low	500 🥳	PR	ns	
t _{RLAL}		REQ Out Low to ACK In Low	(A)	M P	ns	
t _{DVAL}		Data In Valid to ACK In Low	0	A 13 .	ns	
t _{ALRH}		ACK In Low to REQ Out High	10	175	ns	
t _{RHDI}	4	REQ Out High to Data in Invalid	0	-	ns	
t _{RHAH}	F P	REO Out High to ACK in High	0		ns	
t _{AHPC}	13.00	ACK in High to Phase Change Out	0		ns	
t _{AHRL}	M	ACK In High to REQ Out Low	0	175	ns	



NOTE: Phase = signals that define the bus phase C/D, MSG

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RECEIVE SYNCHRONOUS INFORMATION TRANSFER IN (ACTING AS AN INITIATOR)

Symbol	Characteristic	Min	Max	Units
t _{DVRL}	Data Valid In to REQ In Low	0	- 4 月	ns
t _{RLDI}	REQ In Low to DATA Invalid	n 45 5		ns
t _{RLRH}	REQ In Low to REQ In High	50		ns
t _{RHRL}	REQ In Highto REQ In Low	50 17	3 2	ns
talah	ACK Out to Mito ACK Out High	Tcyc-10		ns
TAHAL T	ACK Out High to ACK Out Low	Tcyc-25		ns
t _{AHPC}	ACK Out High to Phase Change	0		ns

Parameters $t_{\rm SHPC}$, $t_{\rm ILDT}$, and $t_{\rm PCRL}$ are also applicable and are identical to those in Receive Asynchronous Information Transfer In (Acting as an Initiator), top of page 37.